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Science: Total Energy and Force Methods**

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**Berthe-Salpeter equation without empty electronic states applied to charge-transfer
excitations**

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Outline

Density matrix
formulation of
BSE

Dielectric
matrices

Practical im-
plementation

Bulk systems

Silicon
nanoclusters

Charge-
transfer
excitations

Conclusions

Additional
material

Solution of the Bethe-Salpeter equation without empty electronic states applied to charge transfer excitations

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Acknowledgments

Outline

Density matrix
formulation of
BSE

Dielectric
matrices

Practical im-
plementation

Bulk systems

Silicon
nanoclusters

Charge-
transfer
excitations

Conclusions

Additional
material

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- Deyu Lu (UC Davis, now at BNL)
- Huy-Viet Nguyen (UC Davis)
- Tuan Anh Pham (UC Davis)
- Giulia Galli (UC Davis)

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Outline

Outline

Density matrix
formulation of
BSE

Dielectric
matrices

Practical im-
plementation

Bulk systems

Silicon
nanoclusters

Charge-
transfer
excitations

Conclusions

Additional
material

- Density matrix formulation of the Bethe-Salpeter equation
- The standard electron-hole representation of density matrices
- Elimination of the empty states
- Calculation of dielectric matrices and GW energy levels
- Practical implementation
- Optical spectra of bulk materials: Silicon and diamond
- Application to a 1nm silicon nanocluster
- Application to charge-transfer excitations
- Preliminary GW results

Density matrix formulation of the Bethe-Salpeter equation

The starting point of our derivation is the **Quantum-Liouville equation** for the **COHSEX** density matrix:

$$i\frac{d\hat{\rho}(t)}{dt} = [\hat{H}_{COHSEX}(t), \hat{\rho}(t)]$$

where the Hamiltonian contains a non-local self-energy:

$$\begin{aligned} \hat{H}_{COHSEX}(t)\phi_i(\mathbf{r}, t) = & \left[-\frac{1}{2}\nabla^2 + v_H(\mathbf{r}, t) + v_{ext}(\mathbf{r}, t) \right] \phi_i(\mathbf{r}, t) \\ & + \int \Sigma_{COHSEX}(\mathbf{r}, \mathbf{r}', t) \phi_i(\mathbf{r}', t) d\mathbf{r}' \end{aligned}$$

COHSEX=**C**oulomb **H**ole (plus) **S**creened **E**xchange

See D. Rocca, D. Lu, and G. Galli, J. Chem. Phys. 133, 164109 (2010); D. Rocca, R. Gebauer, Y. Saad, and S. Baroni, J. Chem. Phys. 128, 154105 (2008)

Outline

Density matrix
formulation of
BSE

Dielectric
matrices

Practical im-
plementation

Bulk systems

Silicon
nanoclusters

Charge-
transfer
excitations

Conclusions

Additional
material

Linearization of the Quantum-Liouville equation

For a small external perturbation we have

$$i\frac{d\hat{\rho}'(t)}{dt} = \left[\hat{H}_{COHSEX}, \hat{\rho}'(t) \right] + \left[\hat{\Sigma}'_{COHSEX}[\hat{\rho}'](t), \hat{\rho}_0 \right] + \left[\hat{v}'_{ext}(t), \hat{\rho}_0 \right]$$

that can be formally written as

$$i\frac{d\hat{\rho}'(t)}{dt} = \mathcal{L} \cdot \hat{\rho}'(t) + [\hat{v}'_{ext}(t), \hat{\rho}_0]$$

By Fourier analyzing we obtain

$$(\omega - \mathcal{L}) \cdot \hat{\rho}'(\omega) = [\hat{v}'_{ext}(\omega), \hat{\rho}_0]$$

The eigenvalues of \mathcal{L} are the **EXCITATION ENERGIES** of the system.

Outline

Density matrix
formulation of
BSE

Dielectric
matrices

Practical im-
plementation

Bulk systems

Silicon
nanoclusters

Charge-
transfer
excitations

Conclusions

Additional
material

Electron-hole representation of density matrices

Outline

Density matrix
formulation of
BSE

Dielectric
matrices

Practical im-
plementation

Bulk systems

Silicon
nanoclusters

Charge-
transfer
excitations

Conclusions

Additional
material

$$\hat{\rho}' = \sum_v [|\phi_v\rangle\langle\phi'_v(-\omega)| + |\phi'_v(\omega)\rangle\langle\phi_v|]$$

Since ϕ'_v orbitals are orthogonal to the ground-state orbitals ϕ_v , ONLY the elements of $\hat{\rho}'$ between valence and conduction states (and vice versa) are different from zero.

Electron-hole representation:

$$P_{vc} = \langle\phi_v|\hat{\rho}'|\phi_c\rangle$$

$$P_{cv} = \langle\phi_c|\hat{\rho}'|\phi_v\rangle$$

Explicit representation of density matrices and operators: DFPT

Outline

Density matrix formulation of BSE

Dielectric matrices

Practical implementation

Bulk systems

Silicon nanoclusters

Charge-transfer excitations

Conclusions

Additional material

$$\hat{\rho}' = \sum_v [|\phi_v\rangle\langle\phi'_v(-\omega)| + |\phi'_v(\omega)\rangle\langle\phi_v|]$$

Instead of using explicitly the conduction states we use the **PROJECTOR** onto the conduction state subspace

$$\hat{Q} = 1 - \sum_v |\phi_v\rangle\langle\phi_v|.$$

Density Functional Perturbation Theory representation:

$$x_v^x(\mathbf{r}) = \hat{Q}\hat{\rho}'\phi_v(\mathbf{r}) = \sum_c \phi_c(\mathbf{r})P_{cv}$$

$$x_v^y(\mathbf{r}) = \left(\hat{Q}\hat{\rho}'^\dagger\phi_v(\mathbf{r})\right)^* = \sum_c \phi_c^*(\mathbf{r})P_{vc}.$$

See Baroni *et al.*, Rev. Mod. Phys. 73, 515 (2001)

Dielectric matrix calculation

In order to solve the BSE we need to compute the screened Coulomb potential:

$$W(\mathbf{r}, \mathbf{r}') = \int \epsilon^{-1}(\mathbf{r}, \mathbf{r}'') v_c(\mathbf{r}'', \mathbf{r}') d\mathbf{r}''$$

The standard approach to compute ϵ^{-1} requires a **SUMMATION OVER EMPTY STATES**.

We efficiently compute ϵ^{-1} using an iterative method based on DFPT which **DOES NOT** require calculations of empty states and allows to obtain the eigenvalue decomposition of ϵ :

$$\tilde{\epsilon} = \sum_{i=1}^N \lambda_i |\mathbf{u}_i\rangle \langle \mathbf{u}_i|.$$

See:

H. F. Wilson, F. Gygi, and G. Galli, Phys. Rev. B 78, 113303 (2008)

H.-V. Nguyen and S. de Gironcoli, Phys. Rev. B 79, 205114 (2009)

D. Rocca, D. Lu, and G. Galli, J. Chem. Phys. 133, 164109 (2010)

Outline

Density matrix
formulation of
BSE

Dielectric
matrices

Practical im-
plementation

Bulk systems

Silicon
nanoclusters

Charge-
transfer
excitations

Conclusions

Additional
material

Calculation of GW quasi-particle energies

The eigenvalue decomposition of the dielectric matrix

$$\tilde{\epsilon}(i\omega) = \sum_{i=1}^N \lambda_i(i\omega) |\mathbf{u}_i\rangle \langle \mathbf{u}_i|.$$

can be used to express the expectation value of the GW self-energy

$\Sigma_{GW} = \Sigma_X + \Sigma_C$ as

$$\begin{aligned} \langle \Sigma_C(i\omega) \rangle_n &= \frac{1}{2\pi} \sum_{i=1}^N \int d\omega' (\lambda_i^{-1}(i\omega') - 1) \\ &\quad \times \langle \phi_n(v_c^{\frac{1}{2}} \mathbf{u}_i) | (H^0 - i(\omega - \omega'))^{-1} | \phi_n(v_c^{\frac{1}{2}} \mathbf{u}_i) \rangle \end{aligned}$$

- Real frequency results are obtained through analytic continuation
- The matrix elements can be efficiently computed using the Lanczos algorithm
- **NO empty states are explicitly required**

Outline

Density matrix
formulation of
BSE

Dielectric
matrices

Practical im-
plementation

Bulk systems

Silicon
nanoclusters

Charge-
transfer
excitations

Conclusions

Additional
material

Practical implementation

Outline

Density matrix
formulation of
BSE

Dielectric
matrices

Practical im-
plementation

Bulk systems

Silicon
nanoclusters

Charge-
transfer
excitations

Conclusions

Additional
material

- We compute explicitly the absorption spectra using a generalization of the non-Hermitian Lanczos iterative algorithm. More details in:
[D. Rocca, R. Gebauer, Y. Saad, and S. Baroni, J. Chem. Phys. 128, 154105 \(2008\)](#)
- The new method has been implemented in the QUANTUM ESPRESSO package, which uses a plane-wave basis-set and pseudopotentials
- The current implementation uses a scissor operator:
$$\hat{H}_{QP} \approx \hat{H}_{KS} + \Delta \hat{Q}$$
- Work is in progress to introduce GW quasi-particle corrections
- Details in:
[D. Rocca, D. Lu, and G. Galli, J. Chem. Phys. 133, 164109 \(2010\)](#)

Optical spectra of bulk materials: Silicon

Outline

Density matrix
formulation of
BSE

Dielectric
matrices

Practical im-
plementation

Bulk systems

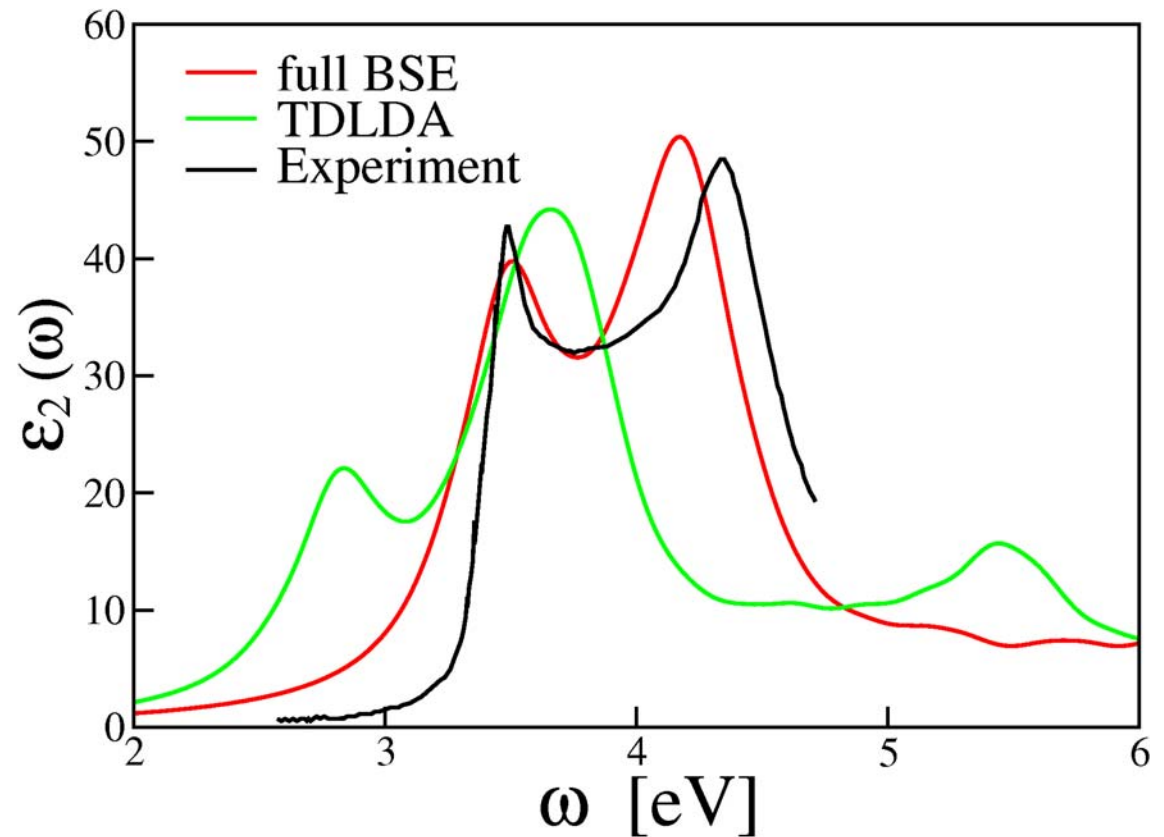
Silicon
nanoclusters

Charge-
transfer
excitations

Conclusions

Additional
material

- $8 \times 8 \times 8$ k mesh
- 18 Ry cut-off



Convergence with respect to the number of eigenvalues in the dielectric matrix

Outline

Density matrix
formulation of
BSE

Dielectric
matrices

Practical im-
plementation

Bulk systems

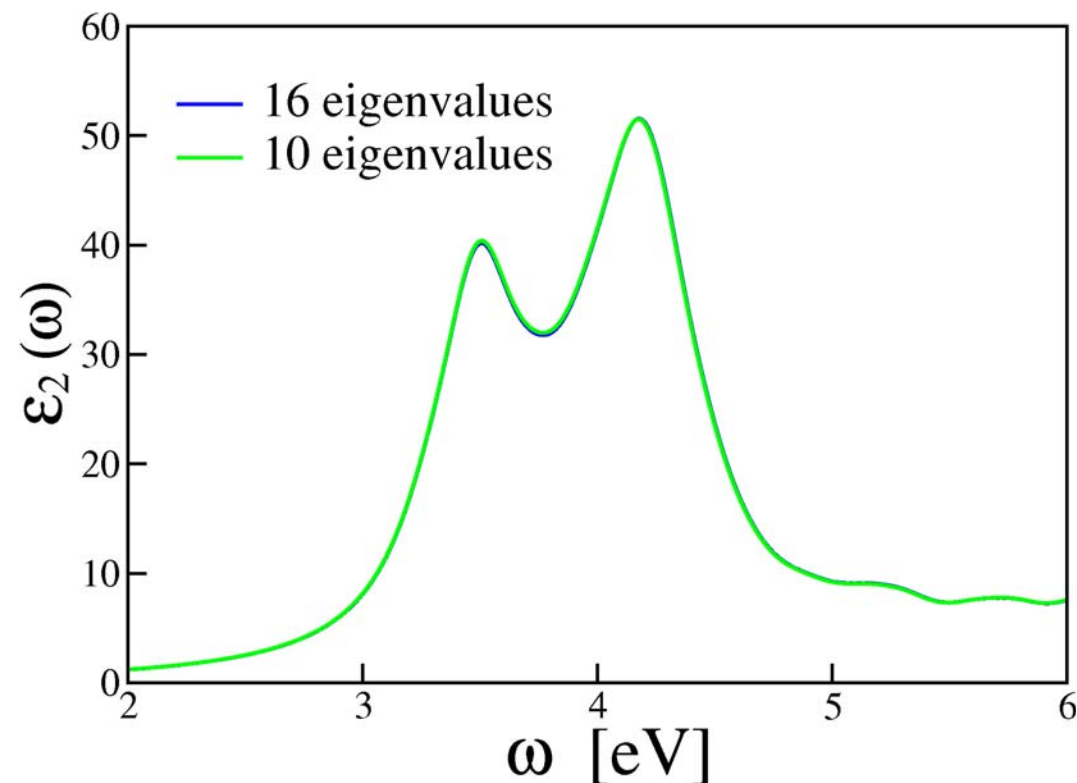
Silicon
nanoclusters

Charge-
transfer
excitations

Conclusions

Additional
material

$$\tilde{\epsilon} = \sum_{i=1}^N \lambda_i |\mathbf{u}_i\rangle \langle \mathbf{u}_i|$$



Tamm-Dancoff approximation (TDA)

Outline

Density matrix
formulation of
BSE

Dielectric
matrices

Practical im-
plementation

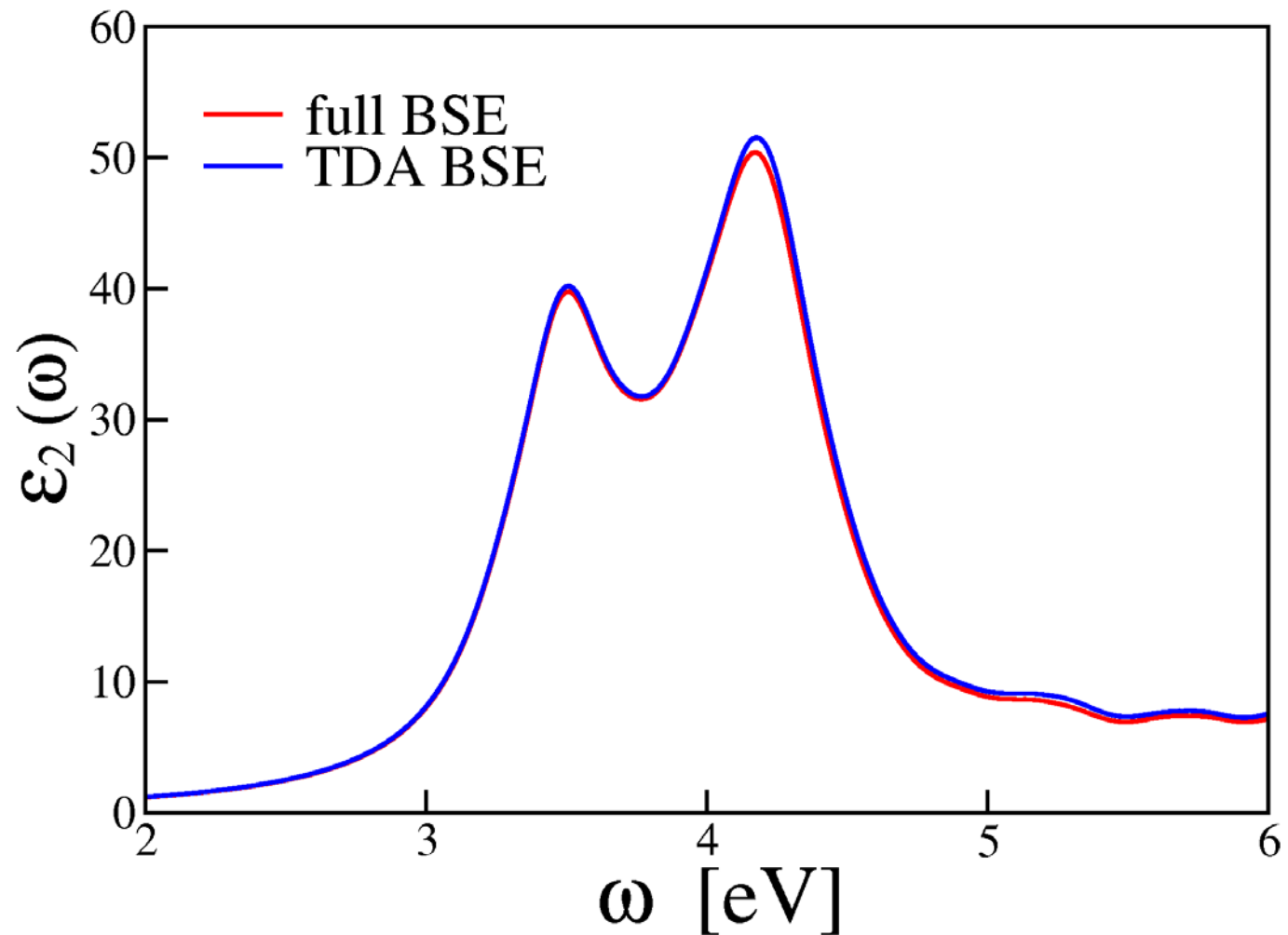
Bulk systems

Silicon
nanoclusters

Charge-
transfer
excitations

Conclusions

Additional
material



Optical spectra of bulk materials: Diamond

Outline

Density matrix
formulation of
BSE

Dielectric
matrices

Practical im-
plementation

Bulk systems

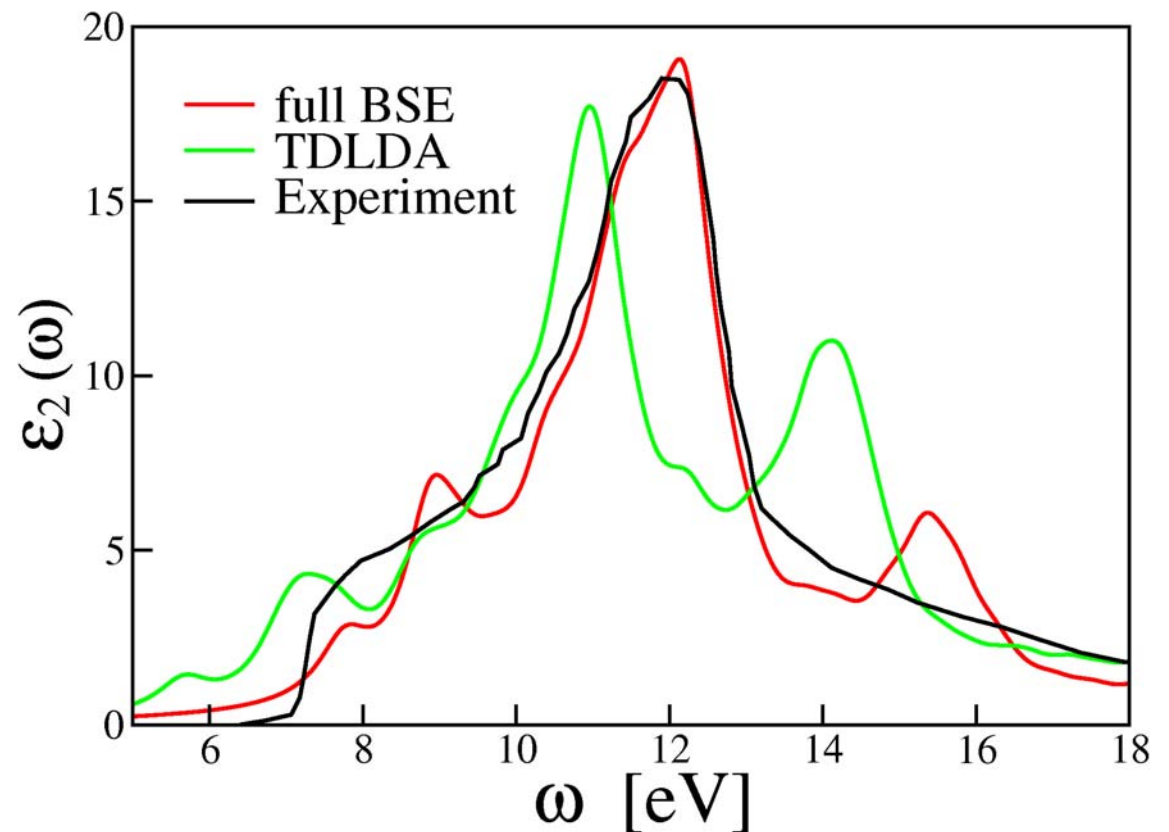
Silicon
nanoclusters

Charge-
transfer
excitations

Conclusions

Additional
material

- $8 \times 8 \times 8$ k mesh
- 40 Ry cut-off



A large system application: absorption spectrum of a 1nm silicon nanocluster

Outline

Density matrix
formulation of
BSE

Dielectric
matrices

Practical im-
plementation

Bulk systems

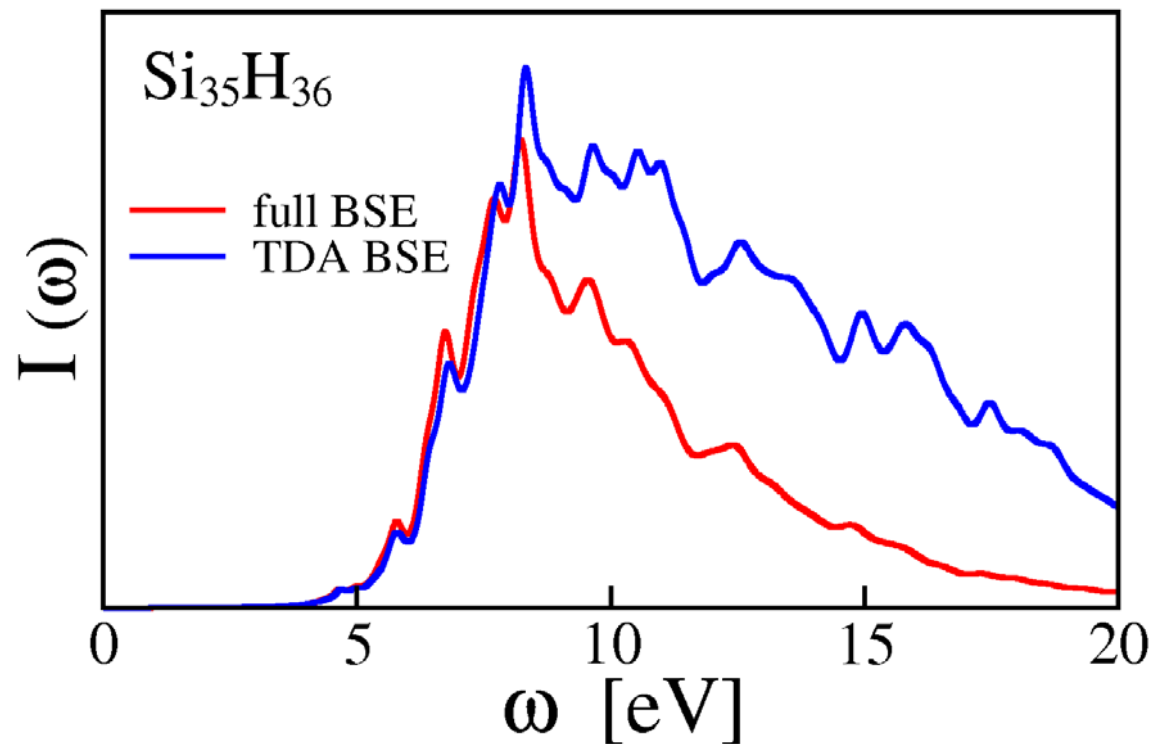
Silicon
nanoclusters

Charge-
transfer
excitations

Conclusions

Additional
material

- 176 electrons
- $40 \times 40 \times 40 a_0^3$ supercell
- 20 Ry cut-off
- 80 Ry for ϵ



TDA = Tamm-Dancoff approximation (Hermitian approximation)

Charge transfer excitations: Study of a dipeptide model

Outline

Density matrix
formulation of
BSE

Dielectric
matrices

Practical im-
plementation

Bulk systems

Silicon
nanoclusters

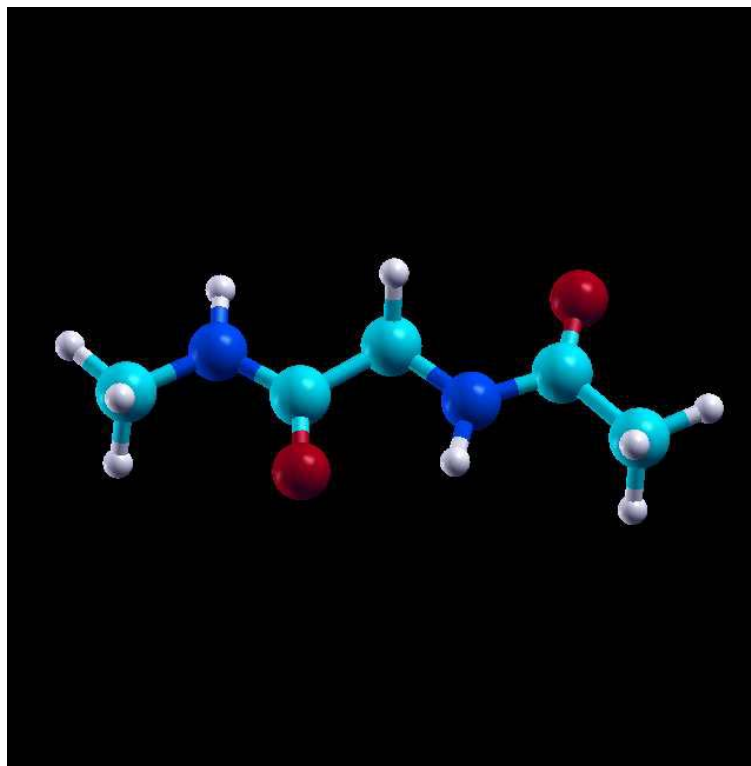
Charge-
transfer
excitations

Conclusions

Additional
material

In order to describe charge-transfer excitations:

- Non-local exchange in the kernel is necessary (JCP 119, 2943 (2003))
- A proper description of the screening has to be included (Bethe-Salpeter equation)



Dipeptide orbitals

Outline

Density matrix
formulation of
BSE

Dielectric
matrices

Practical im-
plementation

Bulk systems

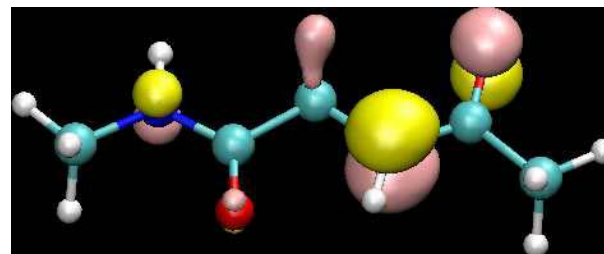
Silicon
nanoclusters

Charge-
transfer
excitations

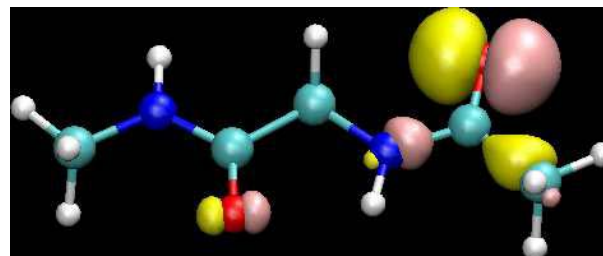
Conclusions

Additional
material

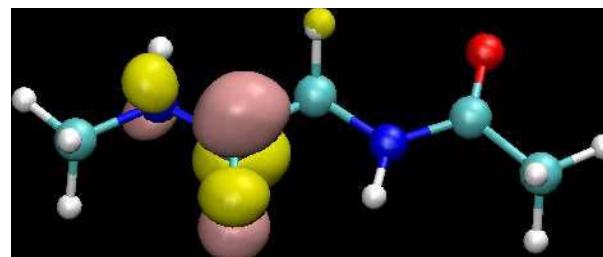
HOMO-1



HOMO



LUMO



Failure of TDLDA to describe charge-transfer excitations

Outline

Density matrix
formulation of
BSE

Dielectric
matrices

Practical im-
plementation

Bulk systems

Silicon
nanoclusters

Charge-
transfer
excitations

Conclusions

Additional
material

Optical Excitation	TDLDA (TDA)	TDLDA	CASPT2 ¹
HOMO → LUMO (CT)	4.61	4.61	8.07
HOMO-1 → LUMO (CT)	5.16	5.15	7.18
HOMO → LUMO+2 (L)	5.30	5.30	5.62
HOMO-2 → LUMO (L)	5.67	5.66	5.79

TDA = Tamm-Dancoff approximation (Hermitian approximation)

CT = Charge-transfer excitation

L = Local excitation

CASPT2 = Complete Active Space with Second-order Perturbation Theory

¹JACS 1998, 120, 10912.

Dipeptide excitation energies: Bethe-Salpeter equation (BSE)

Outline

Density matrix
formulation of
BSE

Dielectric
matrices

Practical im-
plementation

Bulk systems

Silicon
nanoclusters

Charge-
transfer
excitations

Conclusions

Additional
material

Optical Excitation	BSE (TDA)	BSE	CASPT2 ¹
HOMO → LUMO (CT)	<i>o.s. ≈ 0</i>	<i>o.s. ≈ 0</i>	8.07 (<i>o.s. ≈ 0</i>)
HOMO-1 → LUMO (CT)	7.20	7.05	7.18
HOMO → LUMO+2 (L)	5.33	5.30	5.62
HOMO-2 → LUMO (L)	5.63	5.60	5.79

TDA = Tamm-Dancoff approximation (Hermitian approximation)

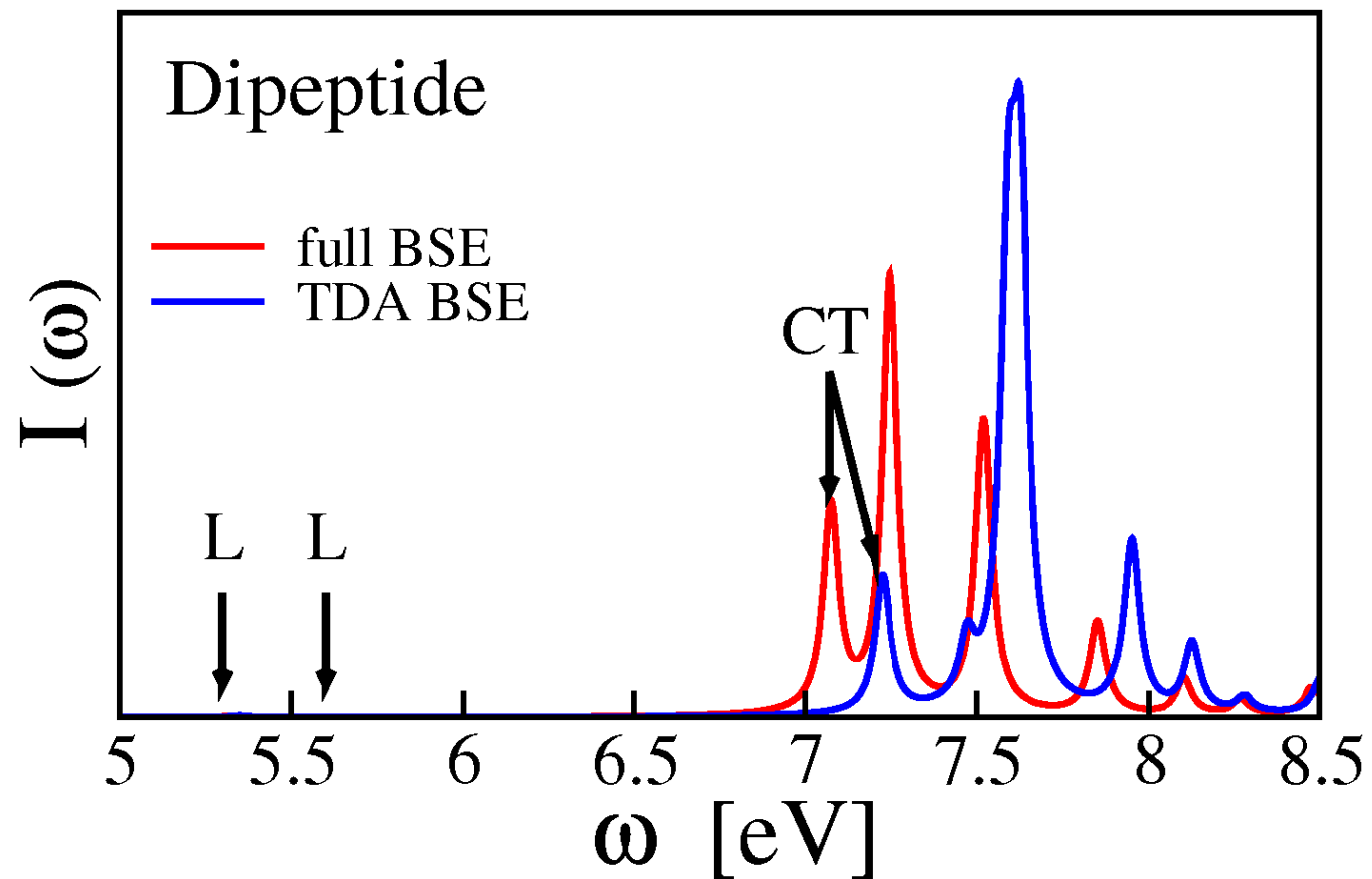
CT = Charge-transfer excitation

L = Local excitation

CASPT2 = Complete Active Space with Second-order Perturbation Theory

¹JACS 1998, 120, 10912.

Dipeptide absorption spectrum



TDA = Tamm-Dancoff approximation (Hermitian approximation)

Outline

Density matrix
formulation of
BSE

Dielectric
matrices

Practical im-
plementation

Bulk systems

Silicon
nanoclusters

Charge-
transfer
excitations

Conclusions

Additional
material

Preliminary GW results: IP for small molecules (eV)

Outline

Density matrix
formulation of
BSE

Dielectric
matrices

Practical im-
plementation

Bulk systems

Silicon
nanoclusters

Charge-
transfer
excitations

Conclusions

Additional
material

Molecule	LDA	PBE [1]	G_0W_0	G_0W_0 [1]	Exp. [1]
CH ₄	9.44	9.43	13.95	14.40	13.60
NH ₃	6.29	6.16	10.59	10.60	10.82
H ₂ O ₂	6.53	6.38	11.05	11.10	11.70
H ₂ O	7.31	7.24	12.25	11.90	12.62

[1] C. Rostgaard, K. W. Jacobsen, and K. S. Thygesen, PRB 81, 085103 (2010)

Work is in progress to interface the BSE and GW codes.

Conclusions

Outline

Density matrix
formulation of
BSE

Dielectric
matrices

Practical im-
plementation

Bulk systems

Silicon
nanoclusters

Charge-
transfer
excitations

Conclusions

Additional
material

- We have introduced a new method in which:
 - Only calculations of occupied states are needed
 - The numerical scalability is comparable to ground-state Hartree-Fock calculations
 - The equations are solved without relying on the Tamm-Dancoff approximation (Hermitian approximation)
 - The spectrum can be calculated in an energy range much larger than with standard approaches
 - Dielectric matrices are obtained using an iterative method based on DFPT (easy storage and inversion)
- The new method has been successfully applied to the description of bulk solids, nanoclusters and charge-transfer excitations

D. Rocca, D. Lu, and G. Galli, J. Chem. Phys. 133, 164109 (2010)

Comparison with the literature

Outline

Density matrix
formulation of
BSE

Dielectric
matrices

Practical im-
plementation

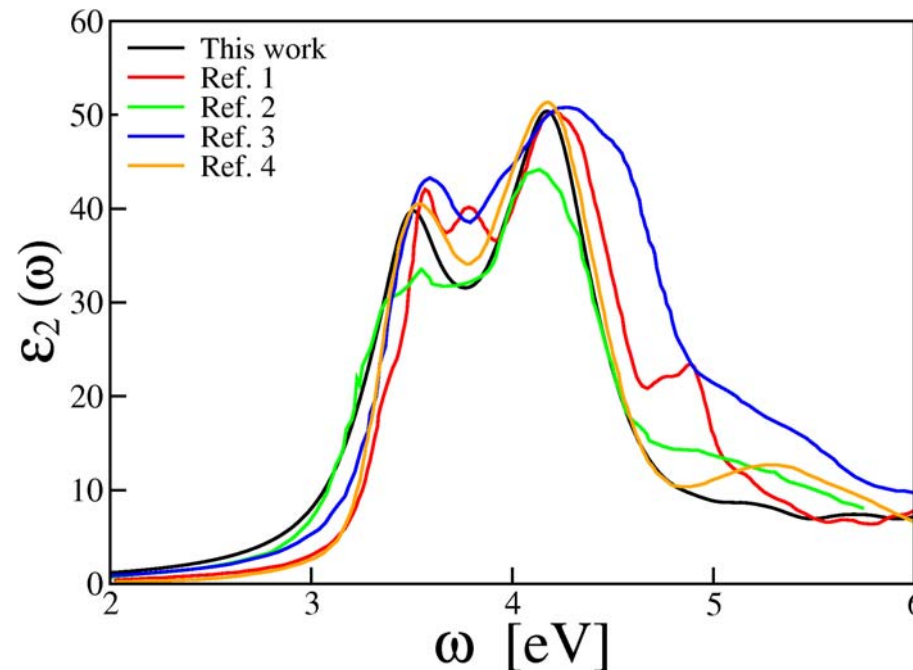
Bulk systems

Silicon
nanoclusters

Charge-
transfer
excitations

Conclusions

Additional
material



- [1] S. Albrecht, L. Reining, R. Del Sole, and G. Onida, PRL 80, 4510 (1998)
- [2] L. X. Benedict, E. L. Shirley, and R. B. Bohn, PRB 57, R9385 (1998)
- [3] M. Rohlfing and S. G. Louie, PRB 62, 4927 (2000)
- [4] L. Reining, V. Olevano, A. Rubio, and G. Onida, PRL 88, 066404 (2002)